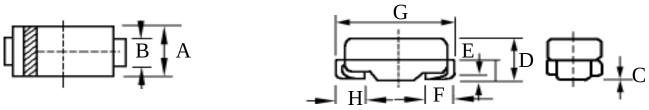
EFM101 – EFM106

1A 片式快速二极管
1A FAST RECOVERY SMA DIODES

型 号 TYPE	印 字 Marking	反向重复峰值电压 V_{RRM}(V)	正 向 平均电流 I_F (A)	正 向 峰值电压 V_F(V)	反 向 峰值电流 I_{RMI}(μA)	正 向 浪涌电流 I_{P8M}(A)	反 向 恢复时间 T_{rr}(ns)	外形尺寸 Package Dimensions
EFM101	EF1	50	1.0	0.95	5.0	30	35	DO – 214AC
EFM102	EF2	100		0.95				
EFM103	EF3	150		0.95				
EFM104	EF4	200		0.95				
EFM105	EF5	300		1.25				
EFM106	EF6	400		1.25				

Trr测试条件: I_F=1A, I_R= 0.5A, I_{RR}= 0.25A
Trr Test Conditions: I_F= 1A, I_R= 0.5A, I_{RR}= 0.25A

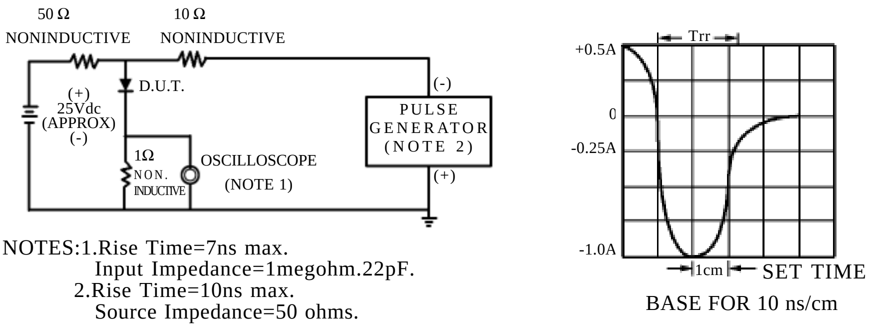


A	B	C	D	E	F	G	H
.110(2.8)	.067(1.7)	.008 MAX	.091(2.3)	.051(1.3)	.059(1.5)	.209(5.3)	.059(1.5)
.086(2.2)	.051(1.3)	(.2)	.067(1.7)	.008(0.2)	.035(0.9)	.185(4.7)	.035(0.9)

DO – 214AC

EFM101 –EFM106
1A 片式快速二极管额定值与特性曲线
RATING & CHARACTERISTIC CURVES OF 1A FAST RECOVERY SMA DIODES

FIG.1-TEST CIRCUIT DIAGRAM AND
REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1.Rise Time=7ns max.
Input Impedance=1megohm.22pF.
2.Rise Time=10ns max.
Source Impedance=50 ohms.

FIG. 2 - TYPICAL FORWARD
CURRENT DERATING CURVE

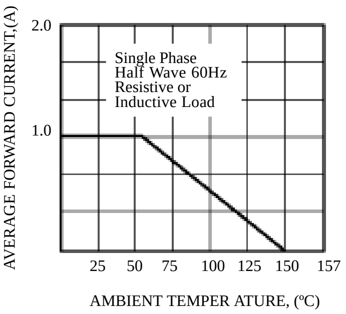


FIG. 3 - TYPICAL REVERSE
CHARACTERISTICS

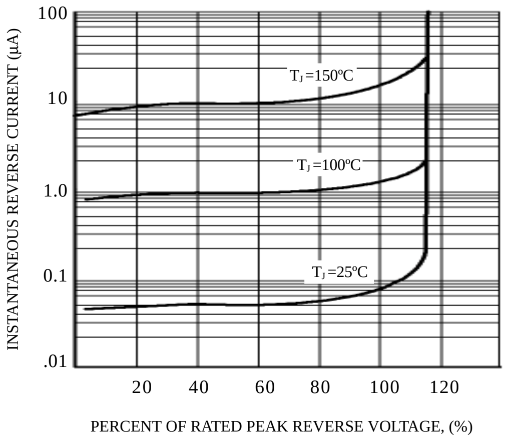


FIG. 4 - TYPICAL INSTANTANEOUS
FORWARD CHARACTERISTICS

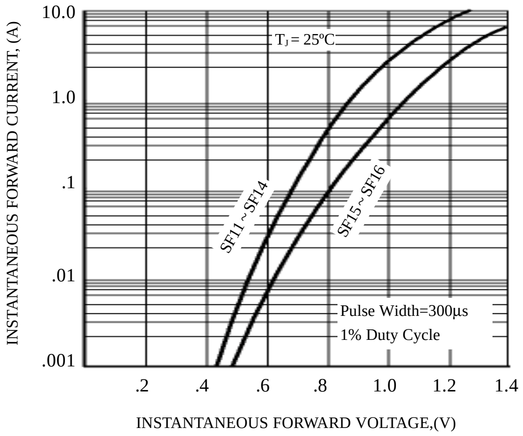


FIG. 5 - MAXINUM NON-REPETITIVE
FOWARD SURGE CURRENT

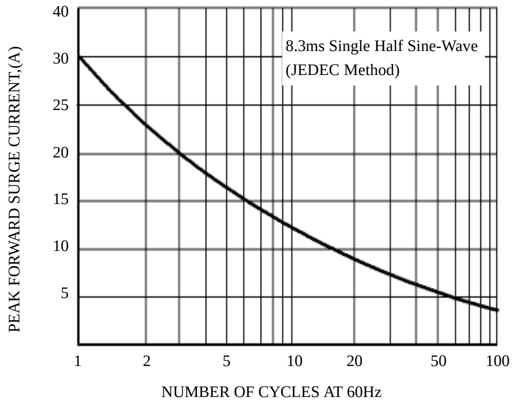


FIG. 6 - TYPICAL JUNCTION CAPACITANCE